

2SB673 2SB674 2SB675

SILICON PNP EPITAXIAL TYPE (PCT PROCESS)
(DARLINGTON POWER)

HIGH POWER SWITCHING APPLICATIONS.
HAMMER DRIVE, PULSE MOTOR DRIVE APPLICATIONS.

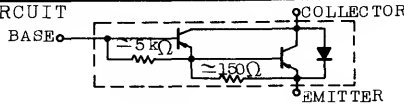
FEATURES:

- High DC Current Gain : $h_{FE}=2000(\text{Min.}) (V_{CE}=-3V, I_C=-3A)$
- Low Saturation Voltage : $V_{CE}(\text{sat})=-1.5V(\text{Max.}) (I_C=-3A)$
- Complementary to 2SD633, 2SD634 and 2SD635.

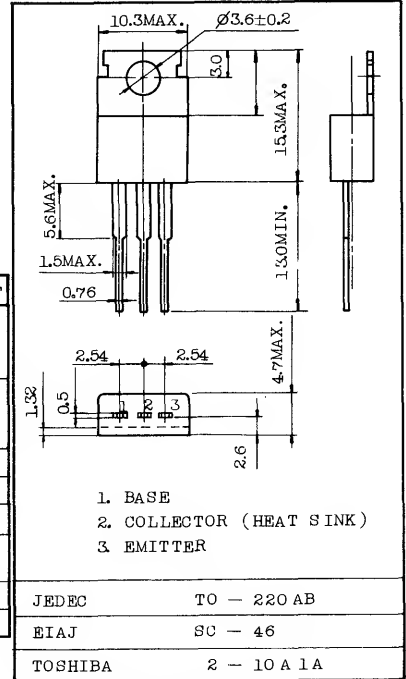
MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage	2SB673	V_{CBO}	-100	V
	2SB674		-80	
	2SB675		-60	
Collector-Emitter Voltage	2SB673	V_{CEO}	-100	V
	2SB674		-80	
	2SB675		-60	
Emitter-Base Voltage		V_{EBO}	-5	V
Collector Current		I_C	-7	A
Base Current		I_B	-0.2	A
Collector Power Dissipation (Tc=25°C)		P_C	40	W
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_{stg}	-55~150	°C

EQUIVALENT CIRCUIT



INDUSTRIAL APPLICATIONS
Unit in mm

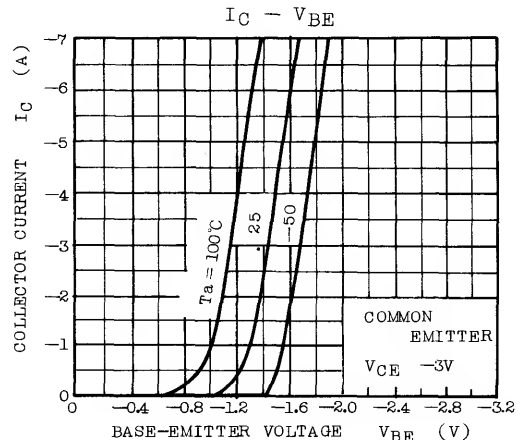
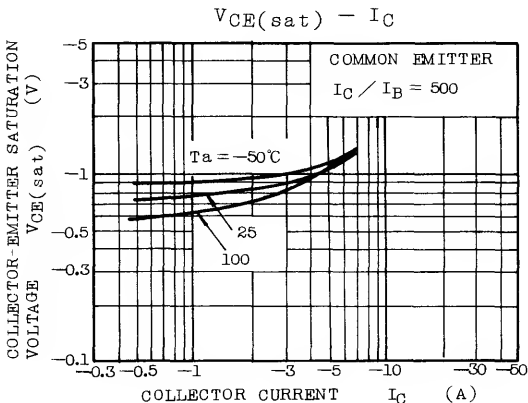
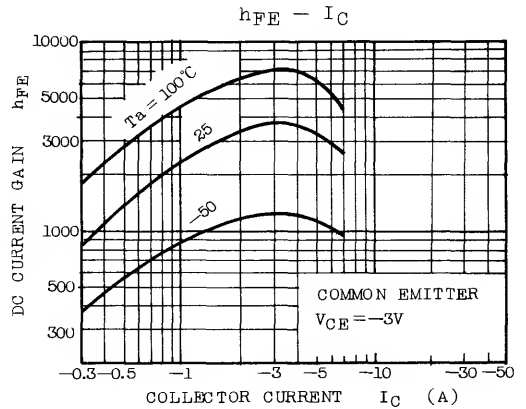
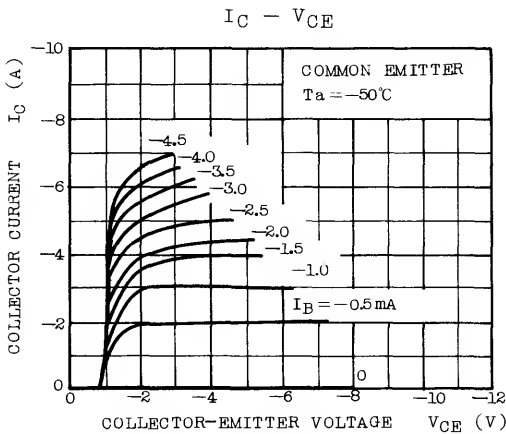
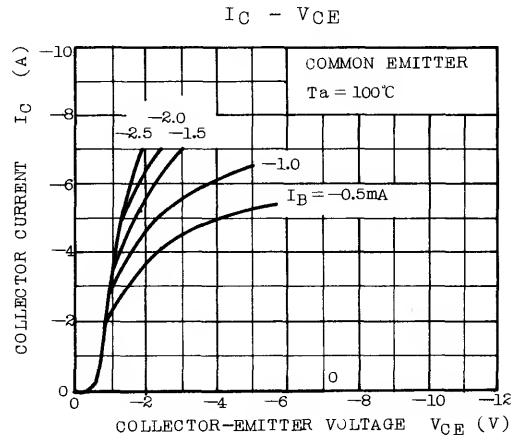
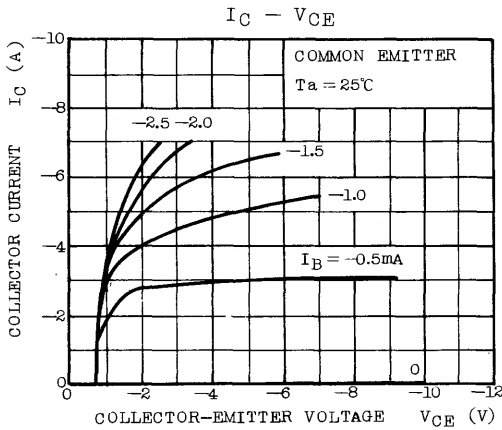


Mounting Kit No. AC75
Weight : 1.9g

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Collector Cut-off Current	2SB673	I_{CBO}	$V_{CB}=-100V, I_E=0$	-	-	-100	μA	
	2SB674		$V_{CB}=-80V, I_E=0$	-	-	-100		
	2SB675		$V_{CB}=-60V, I_E=0$	-	-	-100		
Emitter Cut-off Current		I_{EBO}	$V_{EB}=-5V, I_C=0$	-	-	-4.0	mA	
Collector-Emitter Breakdown Voltage	2SB673	$V_{(BR)CEO}$	$I_C=-50mA, I_B=0$	-100	-	-	V	
	2SB674			-80	-	-		
	2SB675			-60	-	-		
DC Current Gain			$h_{FE}(1)$	$V_{CE}=-3V, I_C=-3A$	2000	-	15000	
			$h_{FE}(2)$	$V_{CE}=-3V, I_C=-7A$	1000	-	-	
Collector-Emitter Saturation Voltage			$V_{CE}(\text{sat})(1)$	$I_C=-3A, I_B=-6mA$	-	-0.95	-1.5	V
			$V_{CE}(\text{sat})(2)$	$I_C=-7A, I_B=-14mA$	-	-1.3	-2.0	
Base-Emitter Saturation Voltage		$V_{BE}(\text{sat})$	$I_C=-3A, I_B=-6mA$	-	-1.55	-2.5	V	
Switching Time	Turn-on Time	t_{on}		-	0.8	-	μs	
	Storage Time	t_{stg}		-	2.0	-		
	Fall Time	t_f		-	-	2.5		-

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